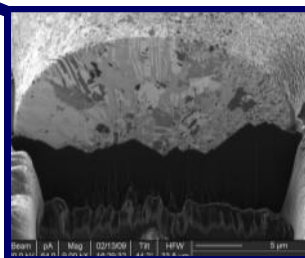
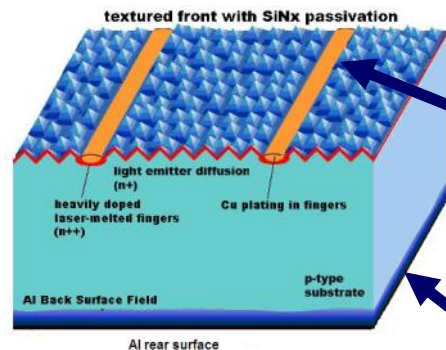


LDSE

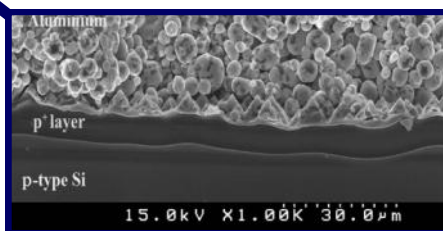
Laser Doping Selective Emitter

(98_0453)

- ◆ Pioneered by UNSW in the mid 1990s
- ◆ Creates high efficiency solar cells
- ◆ 19% + on mono
- ◆ 17% + on multi
- ◆ In 2010 > 20%
- ◆ Uses commercial grade silicon wafers
- ◆ Lower production costs



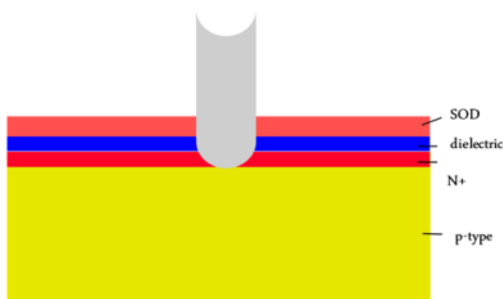
Conformed plating of laser doped regions



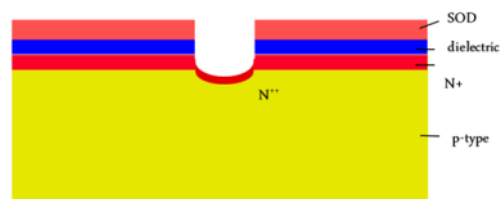
Aluminium rear surfacing



1. Add layer of phosphorus



2. Laser selectively removes dielectric and melts the silicon underneath



3. Simultaneously incorporate dopants into melted region, creating heavily doped region

Choices of add-on technology

Improved Laser Operation (08_2291)	Damage reduced to silicon wafer	Enhances the quality of the laser doping process
Anti-Reflection Coatings (08_2281)	Enhances surface & grain boundary passivation & minimises defect generation during laser doping	Higher efficiencies
Plating (08_2283)	Better performance with improved aspect ratios & reduced costs by using non-precious metals	Less shading, lower costs
Improved Metal Adhesion (08_2290)	Metal better adheres to the surface of the solar cell	Increases durability
Bifacial LDSE (rear contact)	Applying LDSE to front and back surface	Light capture on both sides of the solar cell